



汕头华汕电子器件有限公司

PNP SILICON TRANSISTOR

**H772**

对应国外型号  
2SB772

### 主要用途

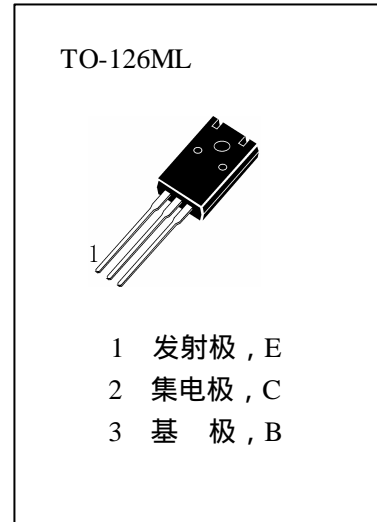
音频放大、开关功率放大

### 极限值 ( $T_a=25$ )

$T_{stg}$	— 贮存温度.....	-55~150
$T_j$	— 结温.....	150
$P_C$	— 集电极功率耗散 ( $T_c=25$ ) .....	10W
$P_C$	— 集电极功率耗散 ( $T_A=25$ ) .....	1W
$V_{CBO}$	— 集电极—基极电压.....	-40V
$V_{CEO}$	— 集电极—发射极电压.....	-30V
$V_{EBO}$	— 发射极—基极电压.....	-5V
$I_C$	— 集电极电流.....	-3A
$I_B$	— 基极电流.....	0.6A

### 电参数 ( $T_a=25$ )

### 外形图及引脚排列



参数符号	符号说明	最小值	典型值	最大值	单位	测试条件
$I_{CBO}$	集电极—基极截止电流			-1	$\mu A$	$V_{CB}=-30V, I_E=0$
$I_{EBO}$	发射极—基极截止电流			-1	$\mu A$	$V_{EB}=-5V, I_C=0$
$h_{FE}$	直流电流增益	60		400		$V_{CE}=-2V, I_C=-1A$
$V_{CE(sat)}$	集电极—发射极饱和压降		-0.3	-0.5	V	$I_C=-2A, I_B=-0.2A$
$V_{BE(sat)}$	基极—发射极饱和压降		-1.0	-2.0	V	$I_C=-2A, I_B=-0.2A$
$C_{ob}$	共基极输出电容		55		pF	$V_{CB}=-10V, I_E=0, f=1MHz$
$f_T$	特征频率		80		MHz	$V_{CE}=-5V, I_E=-0.1A$

### 分档及其标志

R	O	Y	G
60—120	100—200	160—320	200—400



特性曲线

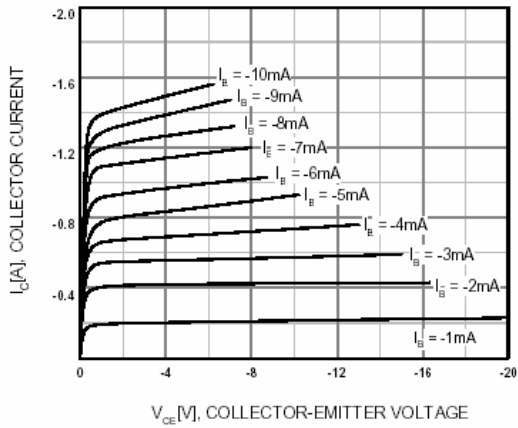


Figure 1. Static Characteristic

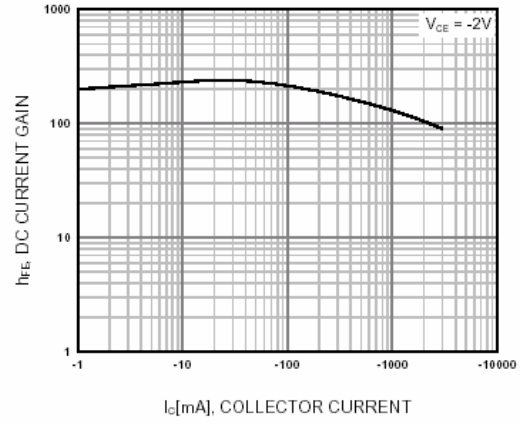


Figure 2. DC current Gain

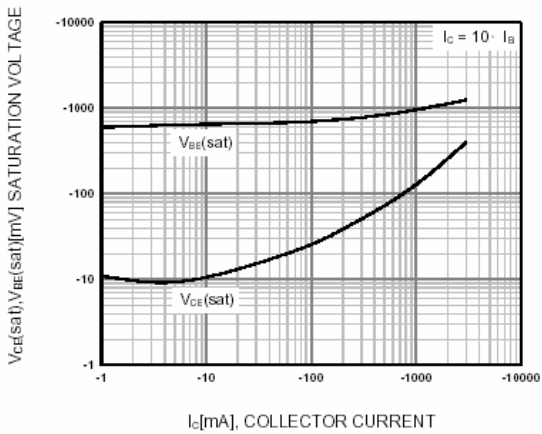


Figure 3. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

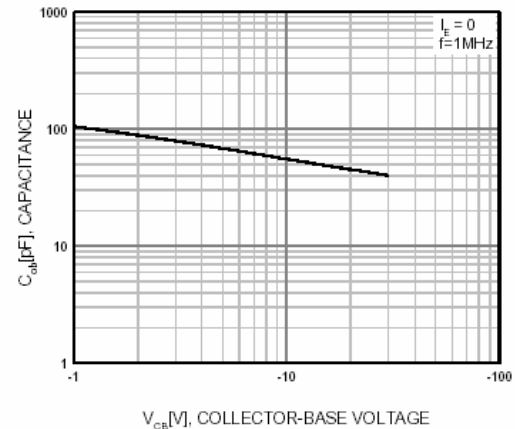


Figure 4. Collector Output Capacitance

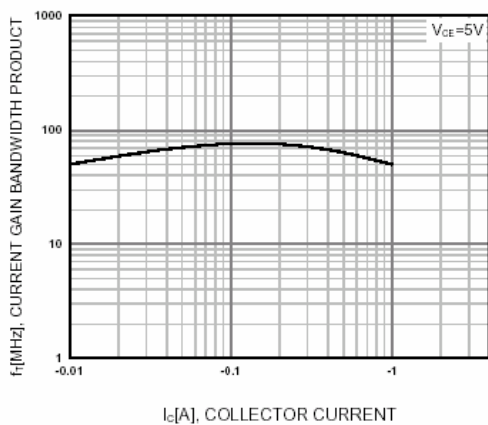


Figure 5. Current Gain Bandwidth Product

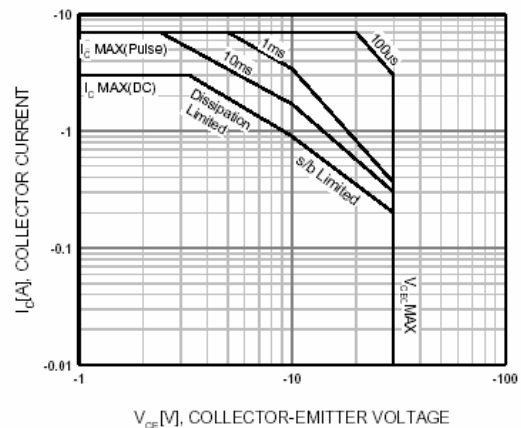


Figure 6. Safe Operating Area



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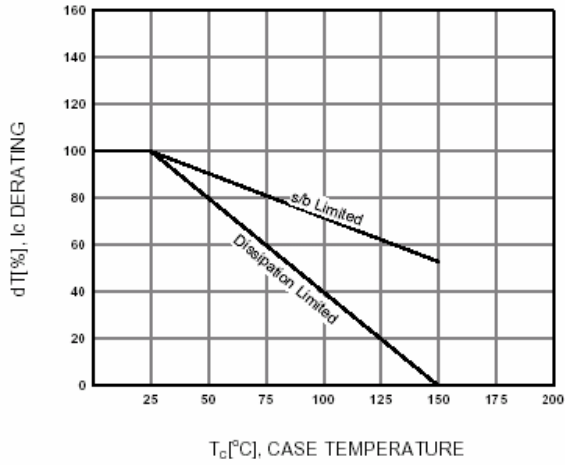


Figure 7. Derating Curve of Safe Operating Areas

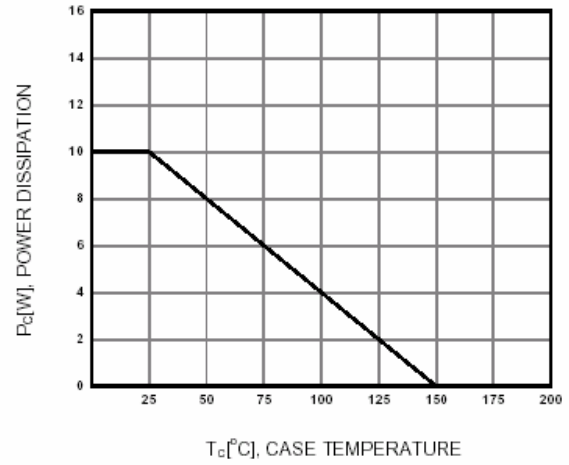


Figure 8. Power Derating